

## AD53041

### FEATURES

- ±50 mA Voltage Programmable Current Range
- Three Selectable Gain Ranges
- 1.7 ns Propagation Delay
- Inhibit Mode Function
- High Speed Differential Inputs for Maximum Flexibility
- Ultrasmall 20-Lead PSOP Package with Built-In Heatsink

### APPLICATIONS

- Automatic Test Equipment
- Semiconductor Test Systems
- Board Test Systems

### PRODUCT DESCRIPTION

The AD53041 is a complete, high speed, current switching load designed for use in linear, digital or mixed signal test systems. Combining a high speed monolithic process with a unique surface mount package, this product attains superb electrical performance while preserving optimum packaging densities in an ultrasmall 20-lead, PSOP package with a built-in heatsink.

Featuring current programmability of up to ±50 mA, the AD53041 is designed to force the device under test to source or sink the programmed  $I_{OH}$  and  $I_{OL}$  currents.  $I_{OH}$  and  $I_{OL}$  currents are determined by applying a corresponding voltage (5 V = 50 mA, 16 mA, 5 mA) to the  $I_{OHPGM}$  and  $I_{OLPGM}$  pins. The voltage-to-current conversion is performed within the AD53041, thus allowing the current levels to be set by a standard voltage out digital-to-analog converter.

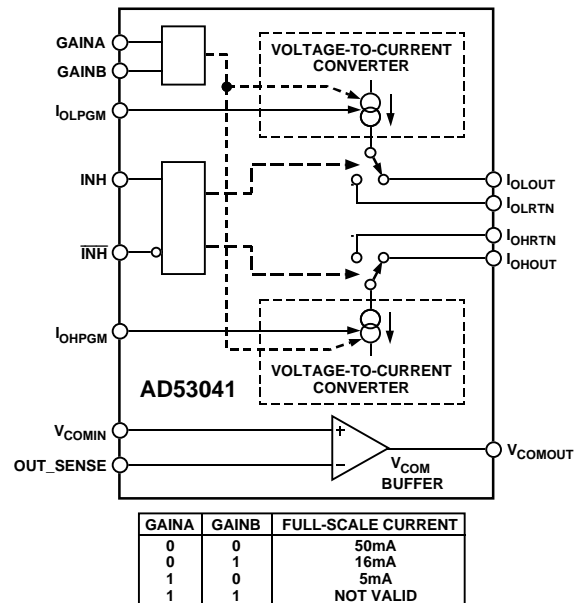
The AD53041 transition from  $I_{OH}$  to  $I_{OL}$  occurs when the output voltage of the device under test slews above or below the programmed threshold or commutation voltage. The commutation voltage is programmable from -2 V to +7 V, covering the large spectrum of logic devices while able to support the large current specifications (48 mA) typically associated with line drivers. To test I/O devices, the active load can be switched into a high impedance state (Inhibit Mode), electrically removing the active load from the path through the Inhibit Mode feature. The active load leakage current in Inhibit is typically 100 nA.

The Inhibit input circuitry is implemented using high speed differential inputs with a common-mode voltage range of -2 V to +3 V and a maximum differential voltage of 3 V. This allows for direct interface to precision differential ECL timing or the simplicity of switching active load from a single ended TTL or CMOS logic source. With switching speeds from  $I_{OH}$  or  $I_{OL}$  into Inhibit of less than 2.0 ns, the AD53041 can be electrically removed from the signal path “on the fly.”

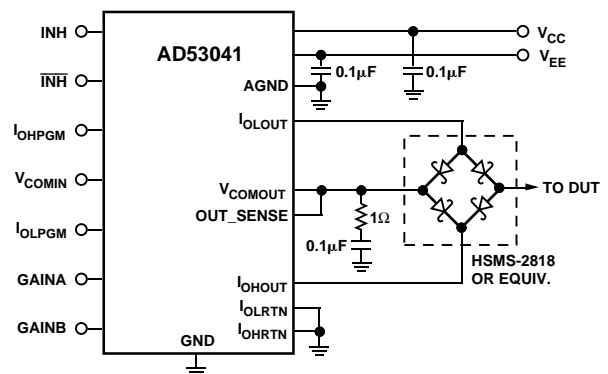
### REV. A

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### FUNCTIONAL BLOCK DIAGRAM



The AD53041 is available in a 20-lead, PSOP package with a built-in-heatsink and is specified to operate over the ambient commercial temperature range from -25°C to +85°C.



NOT SHOWN: THE AGND PINS ARE THE HIGH QUALITY GROUND REFERENCE FOR THE VOLTAGE-TO-CURRENT CONVERTERS. THE GND PINS PROVIDE RETURN PATHS FOR INTERNAL CURRENTS.  $V_{CC}$  IS THE POSITIVE SUPPLY,  $V_{EE}$  IS THE NEGATIVE SUPPLY. ALL GROUND PINS SHOULD BE CONNECTED TO THE SYSTEM ANALOG GROUND PLANE.

Figure 1. Typical Application Circuit

# AD53041—SPECIFICATIONS

(All specifications apply at  $T_j = +85^\circ\text{C} \pm 5^\circ\text{C}$ .  $+V_S = +10.5\text{ V} \pm 3\%$ ,  $-V_S = -5.2\text{ V} \pm 3\%$  unless otherwise specified.  $V_{\text{COMOUT}}$  is bypassed to ground with a series RC consisting of a  $1\ \Omega$  resistor and a  $0.1\ \mu\text{F}$  capacitor, and is also connected directly to  $\text{OUT\_SENSE}$ . All temperature coefficients are characterized over  $T_j = 75^\circ\text{C} - 95^\circ\text{C}$ .)

Parameter	Min	Typ	Max	Units	Test Conditions
<b>INPUT CHARACTERISTICS</b>					
INH, $\overline{\text{INH}}$					
Input Voltage	-2	ECL	0	V	INH, $\overline{\text{INH}} = -2\text{ V}, 0\text{ V}$
Bias Current	-1		1	mA	
GAINA, GAINB					
Input Voltage	0	TTL/CMOS	5	V	GAINA, GAINB = 5 V
Bias Current	0		2	mA	
$I_{\text{OHPGM}}, I_{\text{OLPGM}}$ Voltage Range					
$I_{\text{OH}}$ , 0 to + Full Scale, Any Gain Range	-0.1		5.2	V	$V(I_{\text{OHOUT}}) = -2\text{ V}, 7\text{ V}$
$I_{\text{OL}}$ , 0 to - Full Scale, Any Gain Range	-0.1		5.2	V	$V(I_{\text{OLOUT}}) = -2\text{ V}, 7\text{ V}$
$I_{\text{OHPGM}}, I_{\text{OLPGM}}$ Bias Current	-300		300	$\mu\text{A}$	$V(I_{\text{OHPGM}}) = +5\text{ V}, V(I_{\text{OLPGM}}) = 0\text{ V}$
<b><math>V_{\text{COM}}</math> BUFFER</b>					
Voltage Range	-2		7	V	$\pm 50\text{ mA}$ Output Current
Offset		$\pm 5$		mV	$V_{\text{COM}} = 0\text{ V}$
Offset Drift		0.1		$\text{mV}/^\circ\text{C}$	$V_{\text{COM}} = 0\text{ V}$
Nonlinearity		$\pm 5$		mV	$V_{\text{COM}} = -2\text{ V to } 7\text{ V}$
Input Bias Current	-50		50	$\mu\text{A}$	$V_{\text{COM}} = -2\text{ V to } 7\text{ V}$
Output Resistance		<1		$\Omega$	$V_{\text{COM}} = 0\text{ V}, I_{\text{OUT}} = \pm 50\text{ mA}$
<b>OUTPUT CHARACTERISTICS</b>					
Full-Scale Current Range					
Range 0		50		mA	See Functional Block Diagram
Range 1		16		mA	
Range 2		5		mA	
Offset Error					
Range 0	-1		1	mA	$V(I_{\text{OHPGM}}) = V(I_{\text{OLPGM}}) = 100\text{ mV},$ $V(I_{\text{OHOUT}}) = \pm 2\text{ V}, V(I_{\text{OLOUT}}) = \pm 2\text{ V}$
Range 1	-0.3		0.3	mA	
Range 2	-0.3		0.3	mA	
Offset Drift					
Range 0		1		$\mu\text{A}/^\circ\text{C}$	$V(I_{\text{OHPGM}}) = V(I_{\text{OLPGM}}) = 100\text{ mV},$ $V(I_{\text{OHOUT}}) = V(I_{\text{OLOUT}}) = 0\text{ V}$
Range 1		1		$\mu\text{A}/^\circ\text{C}$	
Range 2		1		$\mu\text{A}/^\circ\text{C}$	
Gain Error					
Range 0		<1		% FSR	Range 0
Range 1		<5		% FSR	
Range 2		<8		% FSR	
Gain Drift					
Range 0		1		$\mu\text{A}/^\circ\text{C}$	Range 0
Range 1		0.5		$\mu\text{A}/^\circ\text{C}$	
Range 2		0.3		$\mu\text{A}/^\circ\text{C}$	
Gain Ratio Drift					
Range 1 to Range 0		0.01		$\%/^\circ\text{C}$	Range 0
Range 2 to Range 0		0.01		$\%/^\circ\text{C}$	
Nonlinearity					
Common-Mode Error		$\pm 0.05$		%FSR	Range 0
PSRR		$\pm 0.1$		%FSR/V	
Range 0, $V(I_{\text{OHPGM}}) = V(I_{\text{OLPGM}}) = 100\text{ mV}$ , Either Supply Over Operating Range					
<b>OUTPUT VOLTAGE RANGE</b>					
$I_{\text{OHOUT}}, I_{\text{OHR TN}}$	-2.5		7.5	V	$I_{\text{OH}} = 50\text{ mA}$
$I_{\text{OLOUT}}, I_{\text{OLR TN}}$	-2.5		7.5	V	$I_{\text{OL}} = 50\text{ mA}$

Parameter	Min	Typ	Max	Units	Test Conditions
<b>LEAKAGE CURRENTS</b>					
$I_{OH}$ Inhibit-Mode Leakage	-1		1	$\mu\text{A}$	Range 0, Bridge Diode Leakage Not Included $V(I_{OHOUT}) = -2.5 \text{ V to } 7.5 \text{ V}$ , Inhibited
$I_{OL}$ Inhibit-Mode Leakage	-1		1	$\mu\text{A}$	$V(I_{OLOUT}) = -2.5 \text{ V to } 7.5 \text{ V}$ , Inhibited
$I_{OH}$ Off-State Leakage	-3		3	$\mu\text{A}$	$V(I_{OHOUT}) = -2.5 \text{ V to } 7.5 \text{ V}$ , $V(I_{OHPGM}) = -0.2 \text{ V}$
$I_{OL}$ Off-State Leakage	-3		3	$\mu\text{A}$	$V(I_{OLOUT}) = -2.5 \text{ V to } 7.5 \text{ V}$ , $V(I_{OLPGM}) = -0.2 \text{ V}$
<b>DYNAMIC PERFORMANCE</b>					
Propagation Delays					
$\pm I_{MAX}$ to Inhibit		1.4		ns	Range 0, $I_{MAX}$ , $R_{LOAD} = 50 \Omega$
Part-to-Part Skew		1		ns	
Inhibit to $\pm I_{MAX}$		1.9		ns	Range 0, $I_{MAX}$ , $R_{LOAD} = 50 \Omega$
Part-to-Part Skew		1		ns	
Propagation Delay Drift		10		$\text{ps}/^\circ\text{C}$	$\pm I_{MAX}$ to Inhibit, Inhibit to $\pm I_{MAX}$
Capacitance		3		pF	$I_{OHOUT}$ or $I_{OLOUT}$ Without Diodes
<b>POWER SUPPLIES</b>					
$-V_S$ to $+V_S$ Range	15.2	15.7	16.2	V	
Positive Supply Range	10.2	10.5	10.8	V	
Negative Supply Range	-5.4	-5.2	-5.0	V	
Positive Supply Current			160	mA	Range 0, $V(I_{OHPGM}) = V(I_{OLPGM}) = 5.0 \text{ V}$ , Active
	10		60	mA	Range 0, $V(I_{OHPGM}) = V(I_{OLPGM}) = 200 \text{ mV}$ , Active
Negative Supply Current			160	mA	Range 0, $V(I_{OHPGM}) = V(I_{OLPGM}) = 5.0 \text{ V}$ , Active
	10		60	mA	Range 0, $V(I_{OHPGM}) = V(I_{OLPGM}) = 200 \text{ mV}$ , Active
Power Dissipation		2.1	2.3	W	$I_{OH} = 50 \text{ mA}$ , $I_{OL} = -50 \text{ mA}$ , Active, $V(I_{OHOUT}) = 7 \text{ V}$ , $V(I_{OLOUT}) = -2 \text{ V}$

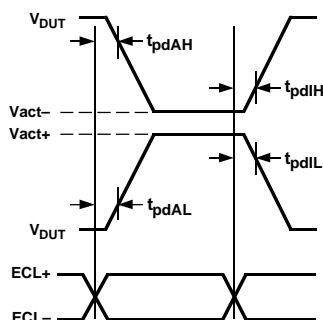
## NOTES

Typical values are not tested or guaranteed.

Specifications subject to change without notice.

**Table I. Active Load Truth Table**  
(Including External Diode Bridge per Figure 1; Scale Factors per Functional Block Diagram)

$V(DUT)$	INH	$\overline{\text{INH}}$	OUTPUT STATES (IFS Is Full-Scale Current Set by GAINA, GAINB)		
			$I_{OH}$	$I_{OL}$	$I(VDUT)$
$< V_{COM}$	0	1	$[V(I_{OHPGM}) \div 5 \text{ V}] \times \text{IFS}$	$[V(I_{OLPGM}) \div 5 \text{ V}] \times \text{IFS}$	$I_{OL}$
$> V_{COM}$	0	1	$[V(I_{OHPGM}) \div 5 \text{ V}] \times \text{IFS}$	$[V(I_{OLPGM}) \div 5 \text{ V}] \times \text{IFS}$	$I_{OH}$
X	1	0	0	0	0



PROPAGATION DELAY LOAD AND TEST CONDITIONS					
PARAMETER	DESCRIPTION	$I_{OL}$	$I_{OH}$	$V_{DUT}$	MEASURE POINT
$t_{pdAH}$	$I_{OL} \text{ Inh} \rightarrow \text{Act}$	50mA	50mA	0V	0.50V
$t_{pdIL}$	$I_{OL} \text{ Act} \rightarrow \text{Inh}$	50mA	50mA	0V	2.00V
$t_{pdAH}$	$I_{OH} \text{ Inh} \rightarrow \text{Act}$	50mA	50mA	5V	4.50V
$t_{pdIH}$	$I_{OH} \text{ Act} \rightarrow \text{Inh}$	50mA	50mA	5V	3.00V

Figure 2. Inhibit Propagation Delay Measurement

# AD53041

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

### Power Supply Voltage

+V <sub>S</sub> to GND	+12 V
-V <sub>S</sub> to GND	-7 V
+V <sub>S</sub> to -V <sub>S</sub>	+17 V
GND to AGND	±0.4 V

### Inputs

INH, $\overline{\text{INH}}$	+6 V, -3 V
INH to $\overline{\text{INH}}$	±3 V
GAINA, GAINB	+6 V, -3 V
GAINA to GAINB	±5 V
V <sub>COMIN</sub>	+8 V, -3 V
I <sub>OH</sub> PGM, I <sub>OL</sub> PGM	+6 V, -1 V

### Outputs

I <sub>OH</sub> OUT, I <sub>OH</sub> RTN	+9 V, -2.5 V
I <sub>OL</sub> OUT, I <sub>OL</sub> RTN	+8 V, -3.5 V
V <sub>COMOUT</sub> Short Circuit Duration	Not Protected <sup>2</sup>

### Environmental

Operating Temperature (Junction)	+175°C
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 sec) <sup>3</sup>	+260°C

### NOTES

<sup>1</sup> Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Absolute maximum limits apply individually, not in combination. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>2</sup> Short circuit to ground or to either supply will result in the destruction of the device.

<sup>3</sup> To ensure lead coplanarity (±0.002 inches) and solderability, handling with bare hands should be avoided and the device should be stored in environments at 24°C ± 5°C (75°F ± 10°F) with relative humidity not to exceed 65%.

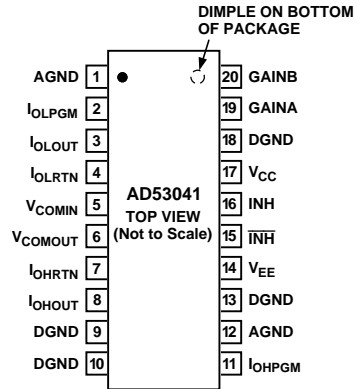
## ORDERING GUIDE

Model	Package Description	Shipment Method, Quantity per Shipping Container	Package Option
AD53041KRP	20-Lead Power SOIC	Tube, 38 Pieces	RP-20

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD53041 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

## PIN CONFIGURATION



NOTES:  
 AGND IS THE HIGH-QUALITY GROUND REFERENCE FOR I<sub>OL</sub>PGM AND I<sub>OH</sub>PGM.  
 DGND IS THE SUPPLY GROUND.

## PACKAGE THERMAL CHARACTERISTICS

Air Flow, FM	θ <sub>JC</sub> , °C/W	θ <sub>JA</sub> , °C/W
0	4	50
50	4	49
400	4	34

## OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

### 20-Lead Thermally Enhanced Power Small Outline Package (PSOP) (RP-20)

